

**International Rectifier**

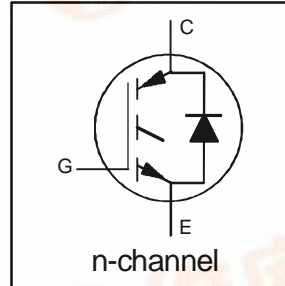
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**IRGBC30FD2**

INSULATED GATE BIPOLAR TRANSISTOR WITH ULTRAFAST SOFT RECOVERY DIODE  
**Features**

Fast CoPack IGBT

- Switching-loss rating includes all "tail" losses
- HEXFRED™ soft ultrafast diodes
- Optimized for medium operating frequency (1 to 10kHz) See Fig. 1 for Current vs. Frequency curve



$V_{CES} = 600V$   
 $V_{CE(sat)} \leq 2.1V$   
@  $V_{GE} = 15V, I_C = 31A$

**Description**

Co-packaged IGBTs are a natural extension of International Rectifier's well known IGBT line. They provide the convenience of an IGBT and an ultrafast recovery diode in one package, resulting in substantial benefits to a host of high-voltage, high-current, motor control, UPS and power supply applications.



**Absolute Maximum Ratings**

	Parameter	Max.	Units
$V_{CES}$	Collector-to-Emitter Voltage	600	V
$I_C @ T_C = 25^\circ C$	Continuous Collector Current	31	A
$I_C @ T_C = 100^\circ C$	Continuous Collector Current	17	
$I_{CM}$	Pulsed Collector Current ①	120	
$I_{LM}$	Clamped Inductive Load Current ②	120	
$I_F @ T_C = 100^\circ C$	Diode Continuous Forward Current	12	
$I_{FM}$	Diode Maximum Forward Current	120	
$V_{GE}$	Gate-to-Emitter Voltage	$\pm 20$	V
$P_D @ T_C = 25^\circ C$	Maximum Power Dissipation	100	W
$P_D @ T_C = 100^\circ C$	Maximum Power Dissipation	42	
$T_J$	Operating Junction and	-55 to +150	°C
$T_{STG}$	Storage Temperature Range		
	Soldering Temperature, for 10 sec.	300 (0.063 in. (1.6mm) from case)	
	Mounting Torque, 6-32 or M3 Screw.	10 lbf•in (1.1 N•m)	

**Thermal Resistance**

	Parameter	Min.	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case - IGBT	—	—	1.2	°C/W
$R_{\theta JC}$	Junction-to-Case - Diode	—	—	2.5	
$R_{\theta CS}$	Case-to-Sink, flat, greased surface	—	0.50	—	
$R_{\theta JA}$	Junction-to-Ambient, typical socket mount	—	—	80	
$Wt$	Weight	—	2 (0.07)	—	g (oz)



# IRGBC30FD2



## Electrical Characteristics @ T<sub>J</sub> = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
V <sub>(BR)CES</sub>	Collector-to-Emitter Breakdown Voltage ③	600	—	—	V	V <sub>GE</sub> = 0V, I <sub>C</sub> = 250μA
ΔV <sub>(BR)CES</sub> /ΔT <sub>J</sub>	Temp. Coeff. of Breakdown Voltage	—	0.69	—	V/°C	V <sub>GE</sub> = 0V, I <sub>C</sub> = 1.0mA
V <sub>CE(on)</sub>	Collector-to-Emitter Saturation Voltage	—	1.8	2.1	V	I <sub>C</sub> = 17A I <sub>C</sub> = 31A I <sub>C</sub> = 17A, T <sub>J</sub> = 150°C V <sub>GE</sub> = 15V See Fig. 2, 5
		—	2.4	—		
		—	2.2	—		
V <sub>GE(th)</sub>	Gate Threshold Voltage	3.0	—	5.5		V <sub>CE</sub> = V <sub>GE</sub> , I <sub>C</sub> = 250μA
ΔV <sub>GE(th)</sub> /ΔT <sub>J</sub>	Temp. Coeff. of Threshold Voltage	—	-11	—	mV/°C	V <sub>CE</sub> = V <sub>GE</sub> , I <sub>C</sub> = 250μA
g <sub>fe</sub>	Forward Transconductance ④	6.1	10	—	S	V <sub>CE</sub> = 100V, I <sub>C</sub> = 17A
I <sub>CES</sub>	Zero Gate Voltage Collector Current	—	—	250	μA	V <sub>GE</sub> = 0V, V <sub>CE</sub> = 600V
		—	—	2500		V <sub>GE</sub> = 0V, V <sub>CE</sub> = 600V, T <sub>J</sub> = 150°C
V <sub>FM</sub>	Diode Forward Voltage Drop	—	1.4	1.7	V	I <sub>C</sub> = 12A See Fig. 13
		—	1.3	1.6		I <sub>C</sub> = 12A, T <sub>J</sub> = 150°C
I <sub>GES</sub>	Gate-to-Emitter Leakage Current	—	—	±100	nA	V <sub>GE</sub> = ±20V

## Switching Characteristics @ T<sub>J</sub> = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
Q <sub>g</sub>	Total Gate Charge (turn-on)	—	27	30	nC	I <sub>C</sub> = 17A V <sub>CC</sub> = 400V See Fig. 8
Q <sub>ge</sub>	Gate - Emitter Charge (turn-on)	—	4.1	5.9		
Q <sub>gc</sub>	Gate - Collector Charge (turn-on)	—	12	15		
t <sub>d(on)</sub>	Turn-On Delay Time	—	72	—	ns	T <sub>J</sub> = 25°C I <sub>C</sub> = 17A, V <sub>CC</sub> = 480V V <sub>GE</sub> = 15V, R <sub>G</sub> = 23Ω Energy losses include "tail" and diode reverse recovery.
t <sub>r</sub>	Rise Time	—	75	—		
t <sub>d(off)</sub>	Turn-Off Delay Time	—	300	450		
t <sub>f</sub>	Fall Time	—	220	350	mJ	See Fig. 9, 10, 11, 18
E <sub>on</sub>	Turn-On Switching Loss	—	0.9	—		
E <sub>off</sub>	Turn-Off Switching Loss	—	2.1	—		
E <sub>ts</sub>	Total Switching Loss	—	3.0	4.6	ns	T <sub>J</sub> = 150°C, See Fig. 9, 10, 11, 18 I <sub>C</sub> = 17A, V <sub>CC</sub> = 480V V <sub>GE</sub> = 15V, R <sub>G</sub> = 23Ω Energy losses include "tail" and diode reverse recovery.
t <sub>d(on)</sub>	Turn-On Delay Time	—	70	—		
t <sub>r</sub>	Rise Time	—	75	—		
t <sub>d(off)</sub>	Turn-Off Delay Time	—	420	—	mJ	See Fig. 9, 10, 11, 18
t <sub>f</sub>	Fall Time	—	480	—		
E <sub>ts</sub>	Total Switching Loss	—	4.7	—		
L <sub>E</sub>	Internal Emitter Inductance	—	7.5	—	nH	Measured 5mm from package
C <sub>ies</sub>	Input Capacitance	—	660	—	pF	V <sub>GE</sub> = 0V V <sub>CC</sub> = 30V f = 1.0MHz See Fig. 7
C <sub>oes</sub>	Output Capacitance	—	100	—		
C <sub>res</sub>	Reverse Transfer Capacitance	—	10	—		
t <sub>rr</sub>	Diode Reverse Recovery Time	—	42	60	ns	T <sub>J</sub> = 25°C See Fig. 14 T <sub>J</sub> = 125°C
		—	80	120		
I <sub>rr</sub>	Diode Peak Reverse Recovery Current	—	3.5	6.0	A	T <sub>J</sub> = 25°C See Fig. 15 T <sub>J</sub> = 125°C
		—	5.6	10		
Q <sub>rr</sub>	Diode Reverse Recovery Charge	—	80	180	nC	T <sub>J</sub> = 25°C See Fig. 16 T <sub>J</sub> = 125°C
		—	220	600		
di <sub>(rec)</sub> /dt	Diode Peak Rate of Fall of Recovery During t <sub>b</sub>	—	180	—	A/μs	T <sub>J</sub> = 25°C See Fig. 17 T <sub>J</sub> = 125°C
		—	120	—		

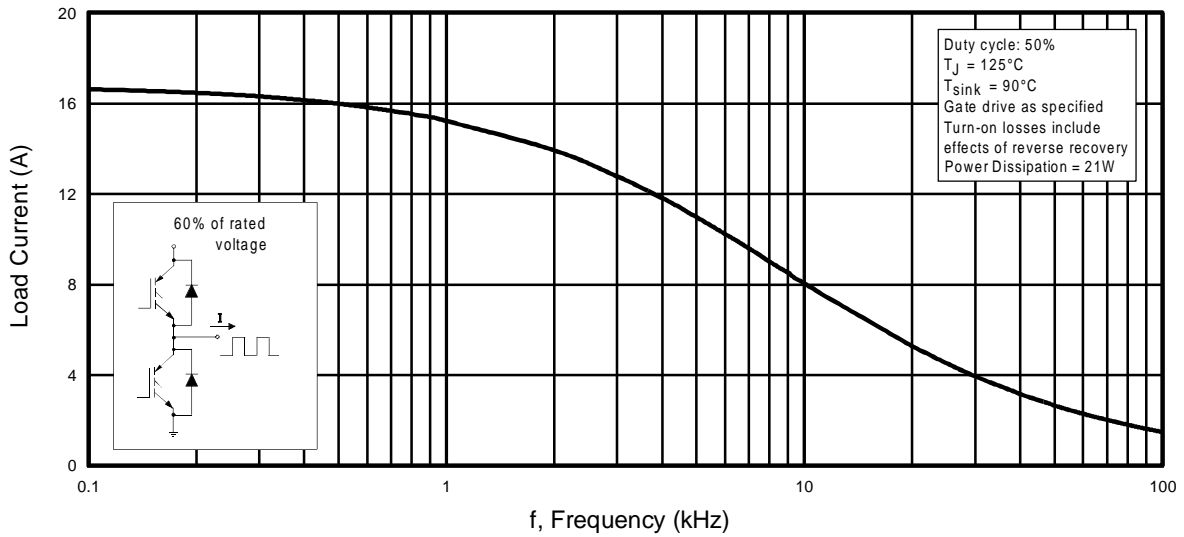
### Notes:

① Repetitive rating; V<sub>GE</sub>=20V, pulse width limited by max. junction temperature. ( See fig. 20 )

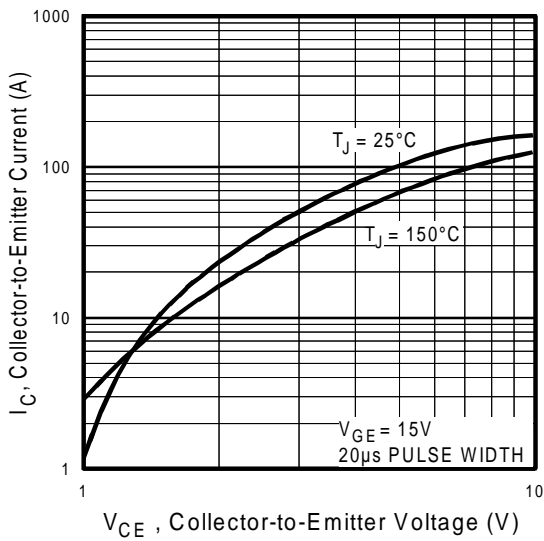
② V<sub>CC</sub>=80%(V<sub>CES</sub>), V<sub>GE</sub>=20V, L=10μH, R<sub>G</sub> = 23Ω, ( See fig. 19 )

③ Pulse width ≤ 80μs; duty factor ≤ 0.1%.

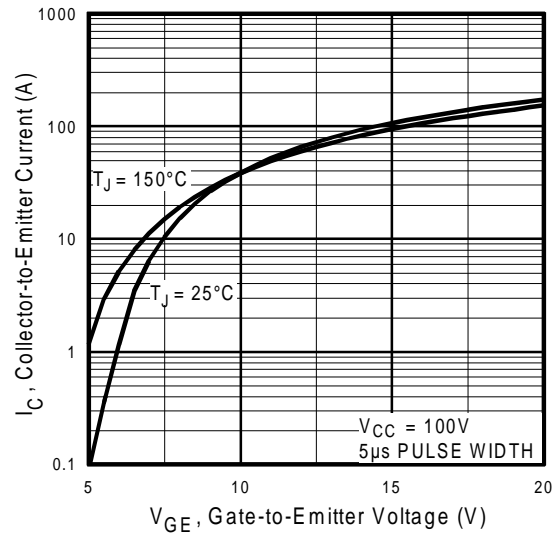
④ Pulse width 5.0μs, single shot.



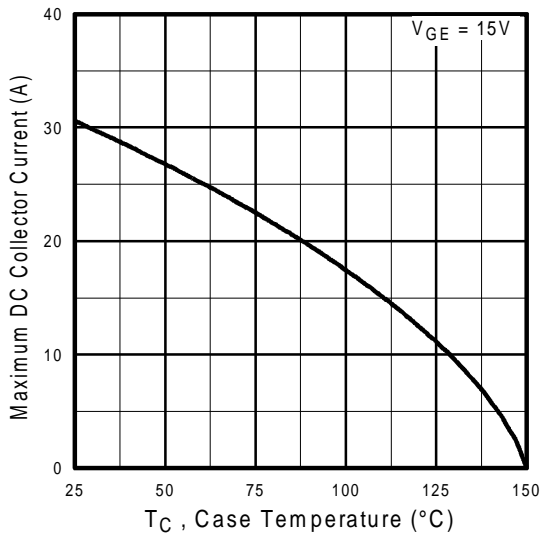
**Fig. 1 - Typical Load Current vs. Frequency**  
(Load Current =  $I_{RMS}$  of fundamental)



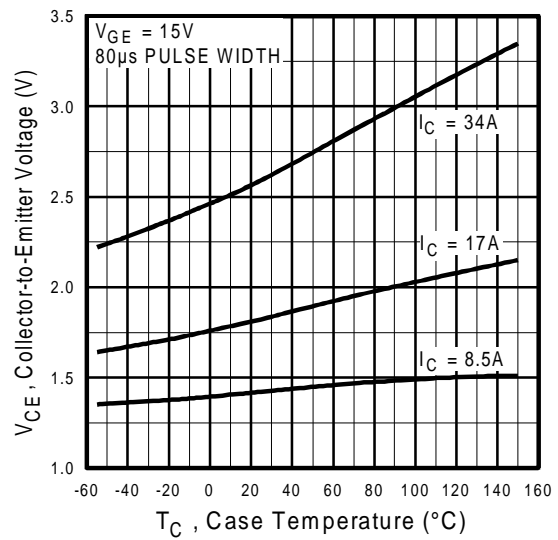
**Fig. 2 - Typical Output Characteristics**



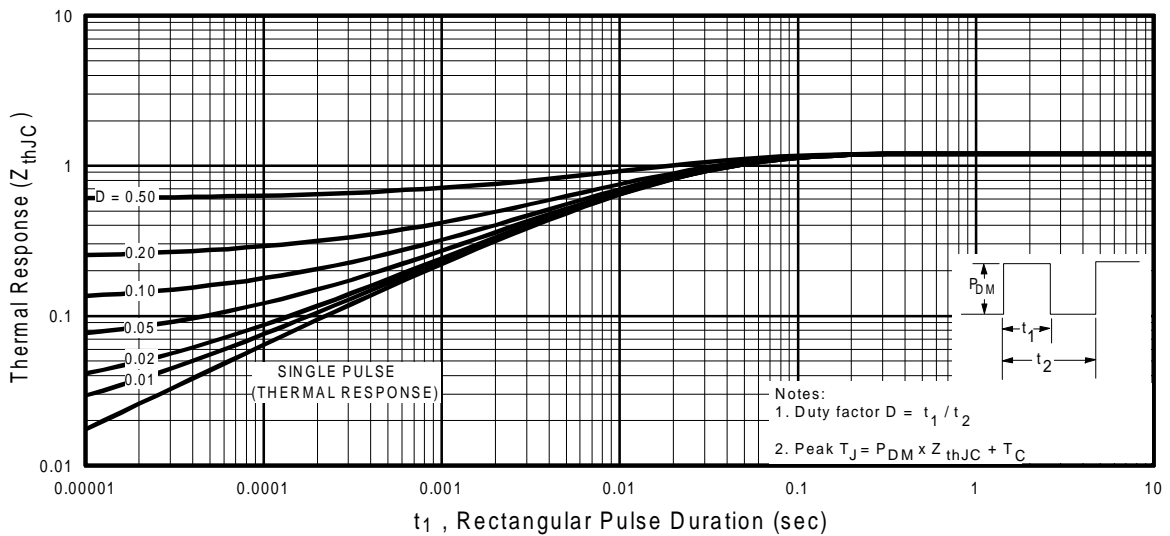
**Fig. 3 - Typical Transfer Characteristics**



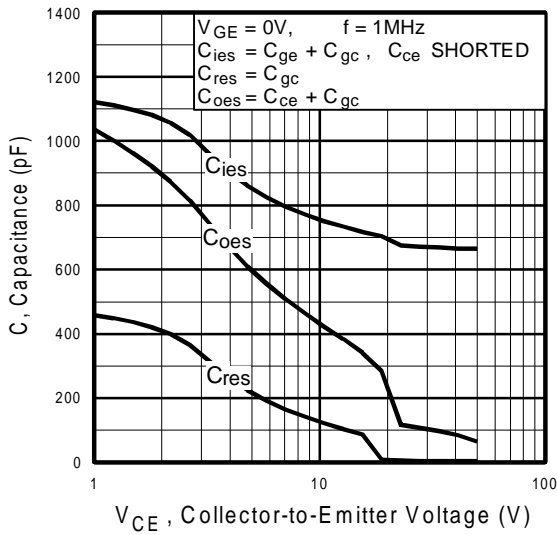
**Fig. 4 - Maximum Collector Current vs. Case Temperature**



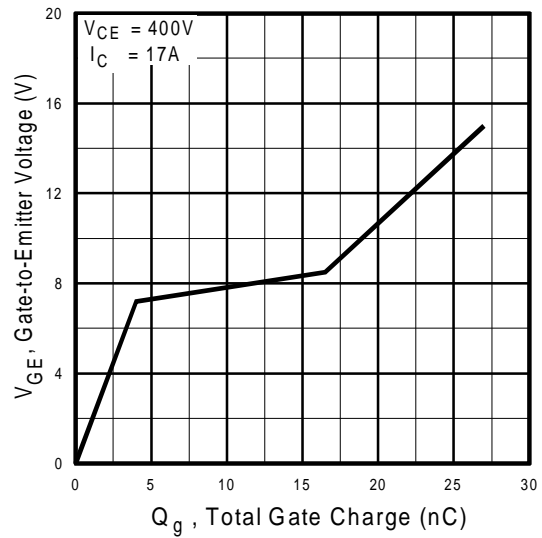
**Fig. 5 - Collector-to-Emitter Voltage vs. Case Temperature**



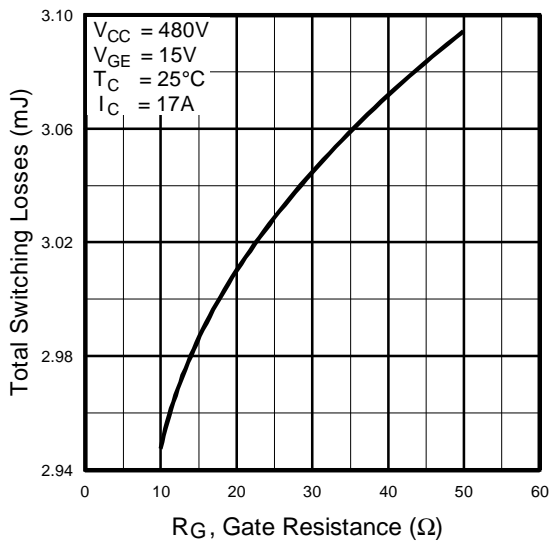
**Fig. 6 - Maximum IGBT Effective Transient Thermal Impedance, Junction-to-Case**



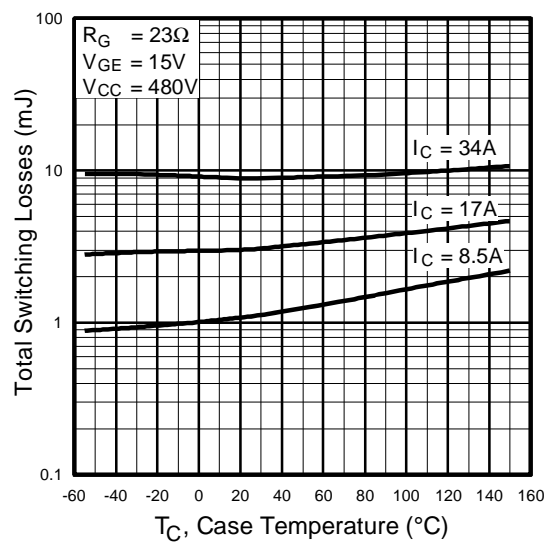
**Fig. 7 - Typical Capacitance vs. Collector-to-Emitter Voltage**



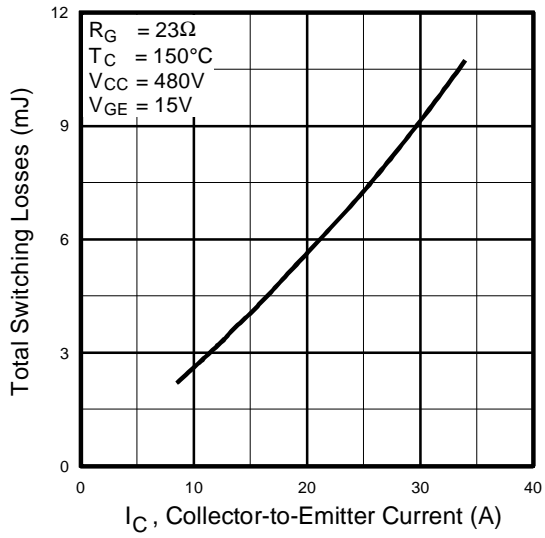
**Fig. 8 - Typical Gate Charge vs. Gate-to-Emitter Voltage**



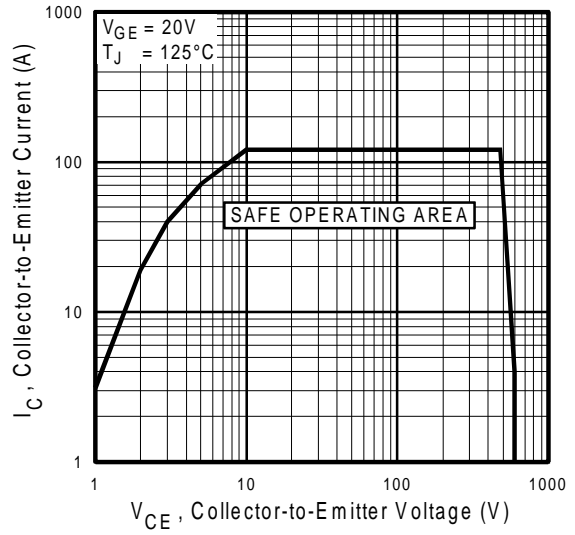
**Fig. 9 - Typical Switching Losses vs. Gate Resistance**



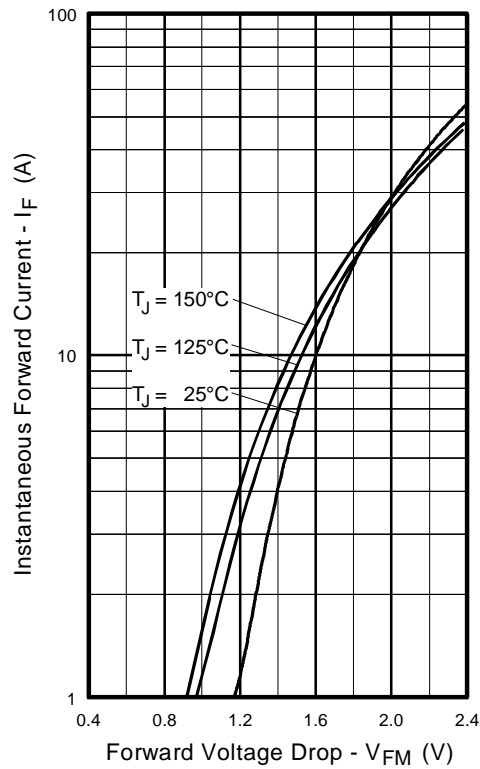
**Fig. 10 - Typical Switching Losses vs. Case Temperature**



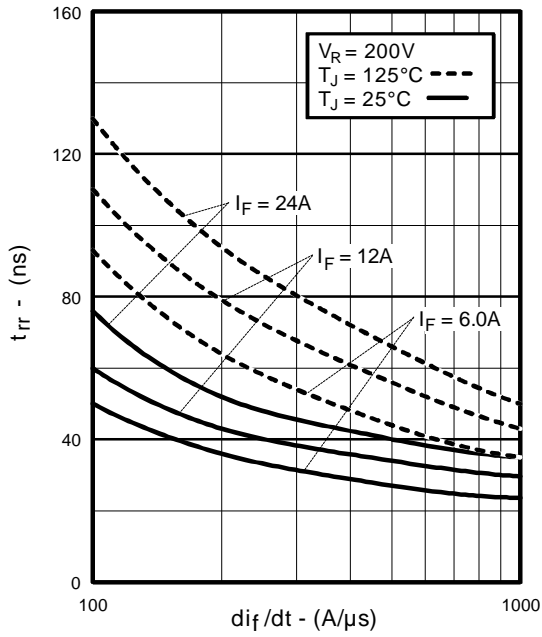
**Fig. 11 - Typical Switching Losses vs. Collector-to-Emitter Current**



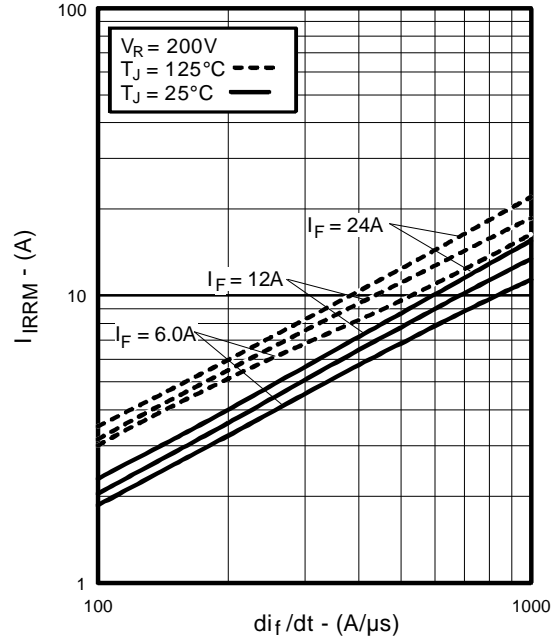
**Fig. 12 - Turn-Off SOA**



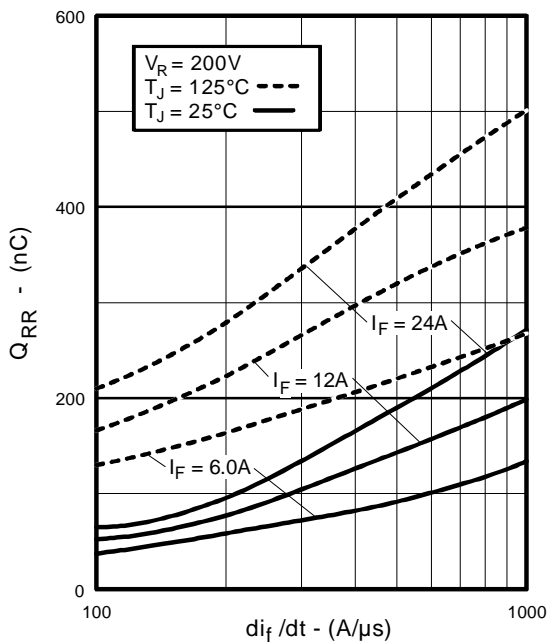
**Fig. 13 - Maximum Forward Voltage Drop vs. Instantaneous Forward Current**



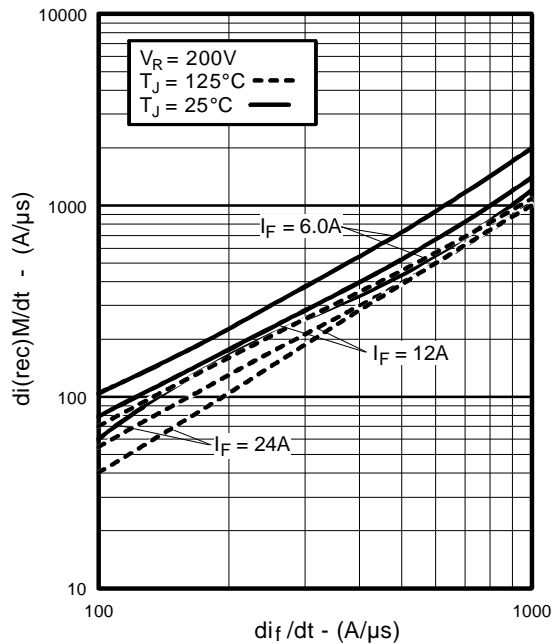
**Fig. 14** - Typical Reverse Recovery vs.  $di/dt$



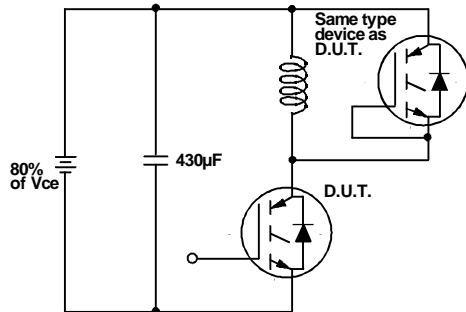
**Fig. 15** - Typical Recovery Current vs.  $di/dt$



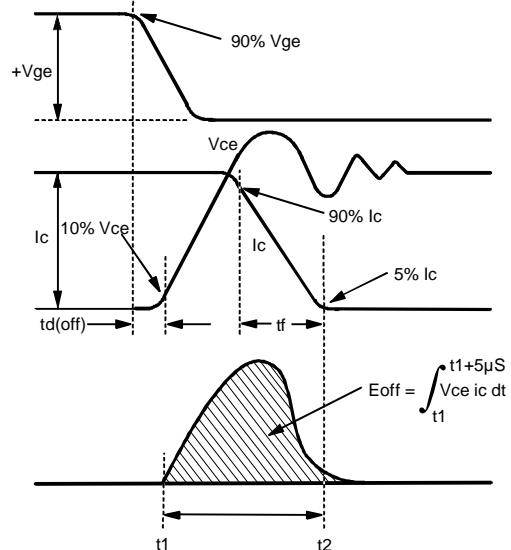
**Fig. 16** - Typical Stored Charge vs.  $di/dt$



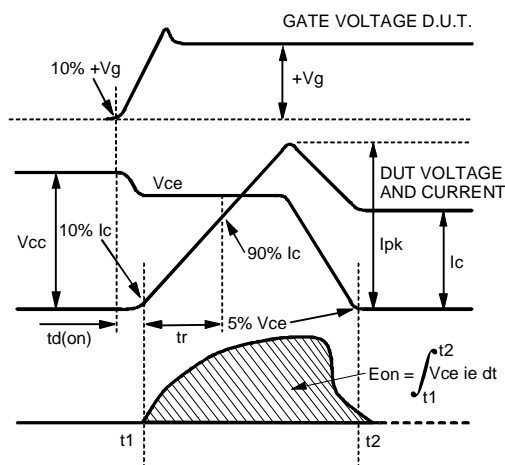
**Fig. 17** - Typical  $di_{(rec)M}/dt$  vs.  $di/dt$



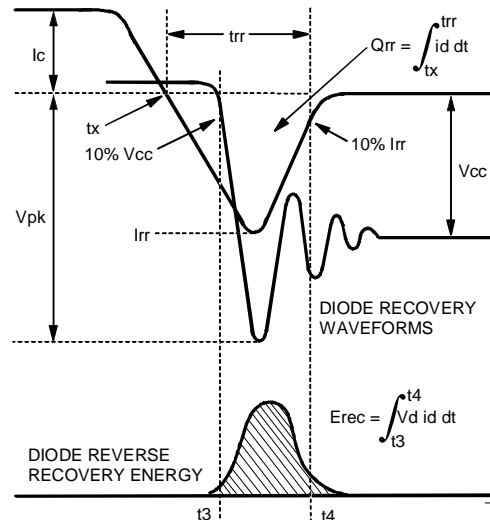
**Fig. 18a** - Test Circuit for Measurement of  $I_{LM}$ ,  $E_{on}$ ,  $E_{off(diode)}$ ,  $t_{rr}$ ,  $Q_{rr}$ ,  $I_{rr}$ ,  $t_{d(on)}$ ,  $t_r$ ,  $t_{d(off)}$ ,  $t_f$



**Fig. 18b** - Test Waveforms for Circuit of Fig. 18a, Defining  $E_{off}$ ,  $t_{d(off)}$ ,  $t_f$



**Fig. 18c** - Test Waveforms for Circuit of Fig. 18a, Defining  $E_{on}$ ,  $t_{d(on)}$ ,  $t_r$



**Fig. 18d** - Test Waveforms for Circuit of Fig. 18a, Defining  $E_{rec}$ ,  $t_{rr}$ ,  $Q_{rr}$ ,  $I_{rr}$

Refer to Section D for the following:  
Appendix D: Section D - page D-6

- Fig. 18e - Macro Waveforms for Test Circuit of Fig. 18a
- Fig. 19 - Clamped Inductive Load Test Circuit
- Fig. 20 - Pulsed Collector Current Test Circuit